TRANSISTOR MOS-FET IGBT DIODE

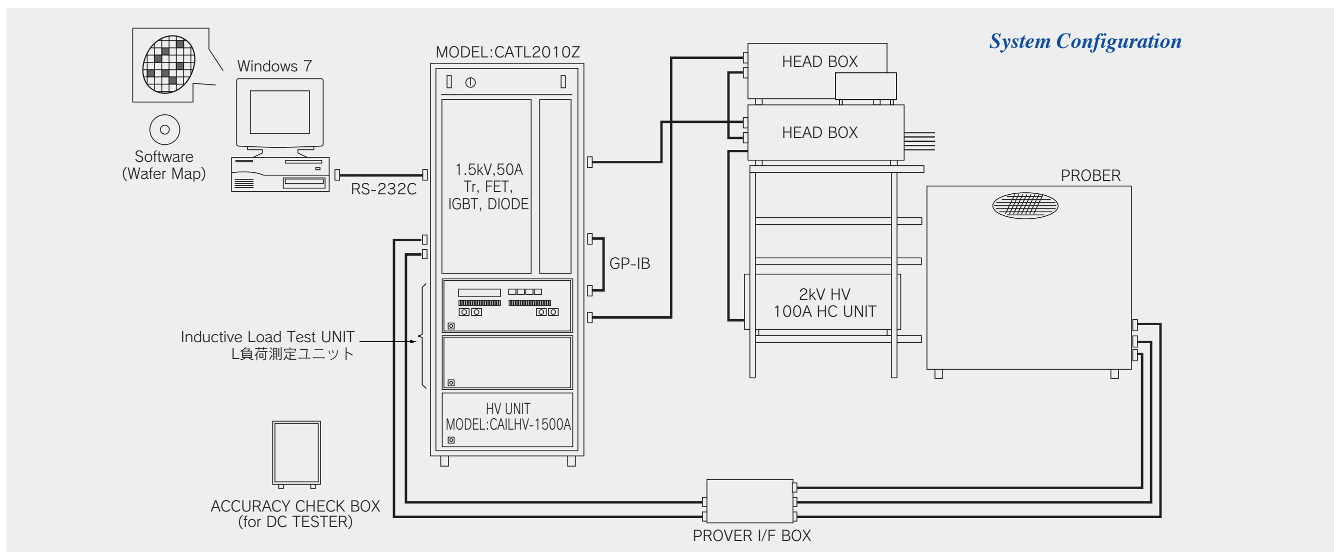
SEMICONDUCTOR TEST SYSTEM 半導体テストシステム

CATL2010Z 2000V 100A

NEW

●CATL2010Z has designed to measure wafer by probe. This test system can measure DC characteristics and inductive load test at one place. It can manage measurement program and result together. It also has wafer map function.

●プローバーによるウェハーの測定器として開発されたシステムで、DC特性とL負荷試験を1ヶ所で測定できます。測定プログラムや測定結果も一元管理ができるとともに、ウェハーマップ機能も装備されいます。



MODEL	CATL2010Z
SOFTWARE	
TEST PROGRAM	TBS(TEST-BY-SORT) Test symbol names can be changed／Host CPU interfaceable by RS-232C
TEST PLAN/SORT PLAN	500/200
BIN OUT	99
DC UNIT	
TEST DEVICES	Transistor, MOS-FET, IGBT, Diode
VOLTAGE	2000V
CURRENT	99.9A
TEST ITEMS	
TRANSISTOR	ICE, ICB, IEB, ILCE, ILCB, ILEB, HICE, HICB, HIEB, BVCE, BVCB, BVEB, IB, HFE, VCESAT, VBESAT, VFBC, VFBE, VFEC, BTON
MOS-FET	IDS, IDG, HIDS, HIDG, IGSX, IGSS, ISGS, BVDS, BVDG, BVSG, VFGD, VFGS, VFSDS, VFSDX, VP, VTH, VDSON, RDSON, IDON, DHIDSS, GMP, GMV, GMI
IGBT	ILGES+, ILGES-, VTHGB1, VTHGB2, VBLMK, VBLMK+, VBLMK-, HVBLMK, HVBLMK+, HVBLMK-, VEmE, VEmE2, VEmER1, VEs1ECS, VEmER2, VGEm, IEmE1, IEs1ECS, IEmE2, BVCEmX2+, BVCEmX2-, BVGESP, VGEI1, VGEI2, HICEX+, HICEX-, HICG, HICG+, HICG-, ICEX+, ICEX-, LIGE, HIGE, IGE, ILCEEs, ThDiVF, VCEsON, VCEON, ICEON,
DIODE	VF, LVF, VR, IR, HIR, LIR
INDUTIVE LOAD TEST	
MEASURABLE DEVICES	NPN/PNP, N/P MOS-FET
IC/ID	0.5A~99.9A
VDD/VCL	1V~399V
Tr	IBF：±000mA~±999mA IBR：∓000mA~∓999mA
FET	VGF：±0.0V~±19.9V VGR：∓0.0V~∓19.9V
Rg	4 circuit select is possible
IH/IL	0.5A~99.9A
VCLAMP	30V~1499V
VLIMIT	30V~1999V
REPEAT	1~19
ON TIME	0.001ms~10.000ms
VSUS	0000V~1999V
DIMENSIONS & WEIGHT	
MAIN UNIT	550(W)×860(D)×1700(H)…320kg
HEAD BOX	430(W)×680(D)×245(H)…40kg
LV+HB	230(W)×590(D)×210(H)…20kg
HB STAND(include HV/HC UNIT)	500(W)×720(D)×990(H)…70kg